FIG.1

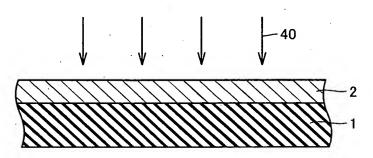


FIG.2

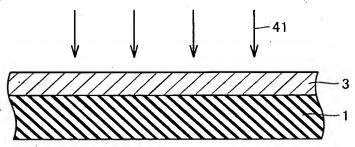


FIG.3

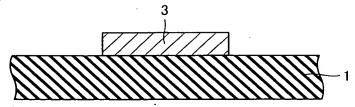


FIG.4

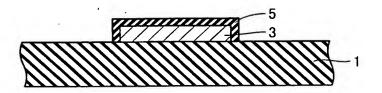


FIG.5

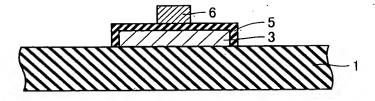


FIG.6

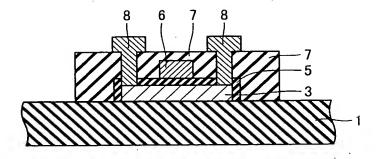
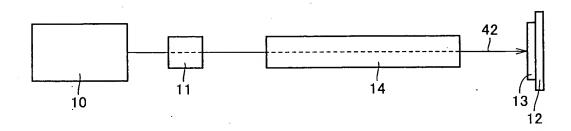


FIG.7



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FIG.8A

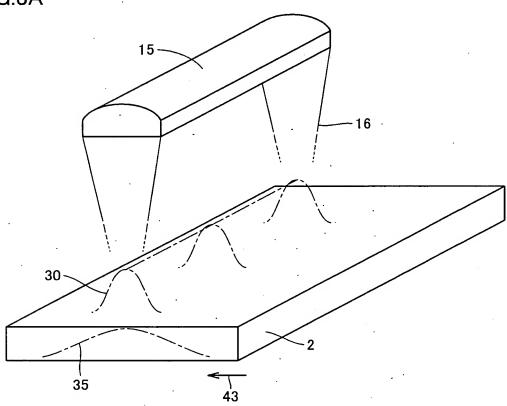


FIG.8B

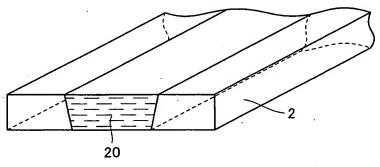


FIG.9

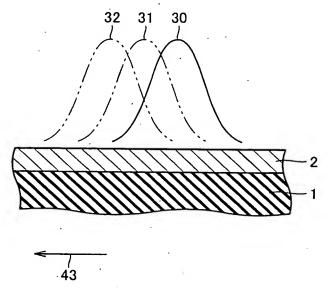


FIG.10A

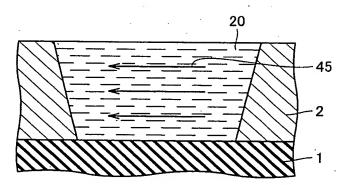


FIG.10B

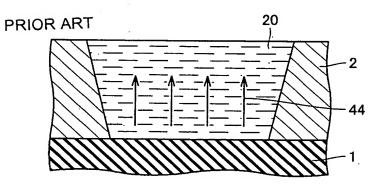


FIG.11

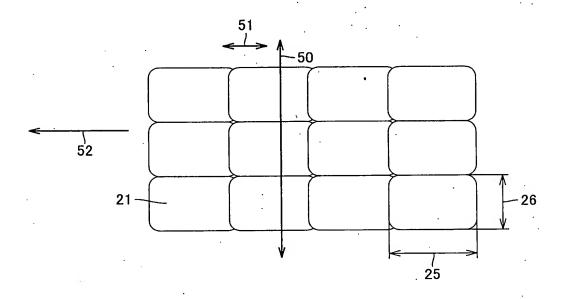
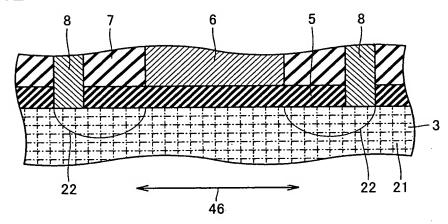


FIG.12

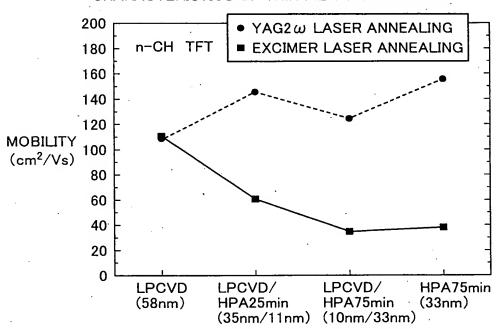


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**FIG.13** 

## CHARACTERISTICS OF THIN FILM TRANSISTORS



CONFIGURATION OF GATE INSULATING FILM

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FIG.14

